

PTO/SB/08A (modified)

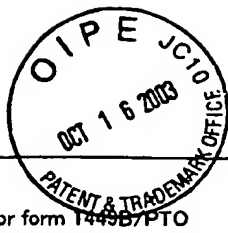
Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	
				Filing Date	
				First Named Inventor	Takashi Matsuoka
				Art Unit	
Examiner Name					
Sheet	1	of	1	Attorney Docket Number	

U.S. PATENT DOCUMENT					
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² <i>(if known)</i>		
MAG		US 5,923,688	JP	07-13-1999	NEC Corporation
		US			
		US			
		US			
		US			
		US			

FOREIGN PATENT DOCUMENT							
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ <i>(if known)</i>			
MAG		JP	08-086978	A	04-02-1996	NTT CORPORATION	ABST
MAG		JP	10-294532	A	11-04-1998	TOSHIBA CORP	ABST
MAG		JP	2002-176196	A	06-21-2002	NGK INSULATORS LTD	ABST

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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PTO/SB/08B (modified)

Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				<i>Complete if Known</i>	
				Application Number	
				Filing Date	
				First Named Inventor Takashi Matsuoka	
				Art Unit	
				Examiner Name	
Sheet	1	of	1	Attorney Docket Number	

OTHER PRIOR ART–NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium catalog, etc.), date, page(s), volume–issue number(s), publisher, city and/or country where published.	Translation ²
MAG		Bernardini et al., "Spontaneous polarization and piezoelectric constants of III–V nitrides", Phys. Rev. B, 56 (1997) R10024	
MAG		Osamura et al., "Fundamental absorption edge GaN, InN and their alloys", Solid State Comm., 11(1972)617	
MAG		Puychevri et al., "Synthesis of III–V semiconductor nitrides by reactive cathodic sputtering", Thin Solid Films, 36(1976)141	
MAG		Tansley et al., "Optical band gap of indium nitride", J Appl. Phys., 59(1986)3241	
MAG		Matsuoka et al., "Wide–Gap Semiconductor (In, Ga) N", International Symposium on GaAs and Related Compounds, (Karuizawa, Japan, 1989); in Inst. Phys. Conf. Ser., 106. pp. 141 – 146	
MAG		Matsuoka, "Phase Separation in Wurtzite In _{1-x-y} Ga _x Al _y N", MRS Internet J. Nitride Semicond. Res. 3,54(1998)	
MAG		Matsuoka et al., "OPTICAL BANDGAP ENERGY OF InN", Extended Abstracts(the 36 th Meeting.); The Japan Society of Applied Physics and Related Societies, pp. 270 (1p–ZN–9) (1998)	
MAG		Matsuoka et al., "OPTICAL BANDGAP ENERGY OF InN", Extended Abstracts(the 49 th Spring Meeting, 2002); The Japan Society of Applied Physics and Related Societies, pp. 392 (29p–ZM–1)	
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Examiner Signature	Marcia Gaby	Date Considered	8/1/2005
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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete if Known

Application Number	10/665,515
Filing Date	September 16, 2003
First Named Inventor	Takashi Matsuoka
Art Unit	
Examiner Name	
Attorney Docket Number	96790P439

Sheet	1	of	2
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U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

**Examiner
Signature**

Maria Cobb

Date _____

Considered

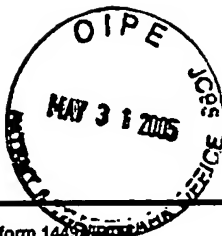
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Based on PTO/SB/08A (08-03) as modified by Blakely, Solokoff, Taylor & Zelman (wtr) 08/11/2003.

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Complete if Known		
			Application Number	10/665,515	
			Filing Date	September 16, 2003	
			First Named Inventor	Takashi Matsuoka	
			Art Unit		
			Examiner Name		
Sheet	2	of	2	Attorney Docket Number	96790P439

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
MAG		"Physics of high-power InGaN/GaN lasers", J. Piprek, et al, IEE Proceedings-Optoelectronics IEE UK, vol. 149, no. 4, 8/4/2002, pgs 145-151	
MAG		"Quantum-Confined Stark Effect in an AlGaIn/GaN/AlGaIn Single Quantum Well Structure", Japanese Journal of Applied Physics, Part 2, vol. 38, no. 8B, 8/15/1999, pgs L914-L916	

Examiner Signature	Maria Gorb	Date Considered	8/11/2005
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